

20 V dual P-channel Trench MOSFET Rev. 1 — 20 June 2012

Product data sheet

1. **Product profile**

1.1 General description

Dual small-signal P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low threshold voltage
- Very fast switching

- Trench MOSFET technology
- 2 kV ElectroStatic Discharge (ESD) protection

1.3 Applications

- Relay driver
- High-speed line driver

- High-side load switch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	r						
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-8	-	8	V
I_D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	<u>[1]</u>	-	-	-3.7	Α
Static charac	teristics (per transistor)						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -1.3 \text{ A}; T_j = 25 \text{ °C}$		-	82	103	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D4 D0
2	G1	gate TR1	6 5 4	D1 D2
3	D2	drain TR2		
4	S2	source TR2		G1 $G2$
5	G2	gate TR2		
6	D1	drain TR1	1 2 3	
7	D1	drain TR1	Transparent top view	S1 S2 017aaa260
8	D2	drain TR2	DFN2020-6 (SOT1118)	

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMDPB85UPE	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1118			

4. Marking

Table 4. Marking codes

Type number	Marking code
PMDPB85UPE	2C

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	tor					
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	<u>[1]</u>	-	-3.7	Α
		$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	<u>[1]</u>	-	-2.9	Α
		$V_{GS} = -4.5 \text{ V}; T_{amb} = 100 ^{\circ}\text{C}$	<u>[1]</u>	-	-1.8	Α
I _{DM}	peak drain current	$T_{amb} = 25 ^{\circ}C$; single pulse; $t_p \le 10 \mu s$		-	-11.6	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	515	mW
			<u>[1]</u>	-	1170	mW
		T _{sp} = 25 °C		-	8330	mW
Source-dra	in diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.2	Α
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Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

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Symbol	Parameter	Conditions		Min	Max	Unit
ESD maximu	m rating					
V _{ESD}	electrostatic discharge voltage	HBM; C = 100 pF; R = 1.5 kΩ	[3]	-	2000	V
Per device						
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

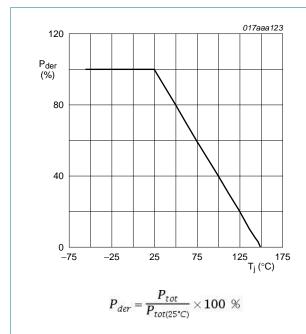


Fig 1. Normalized total power dissipation as a function of junction temperature

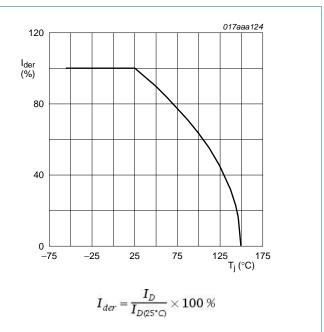


Fig 2. Normalized continuous drain current as a function of junction temperature

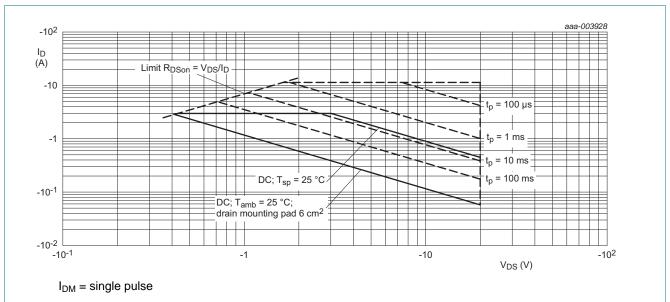


Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R _{th(j-a)}	thermal resistance	in free air	[1]	-	211	243	K/W
	from junction to ambient		[2]	-	93	107	K/W
		in free air; t ≤ 5 s	[2]	-	55	64	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	12	15	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

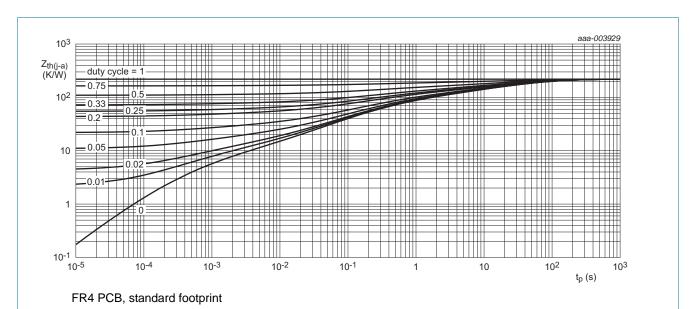
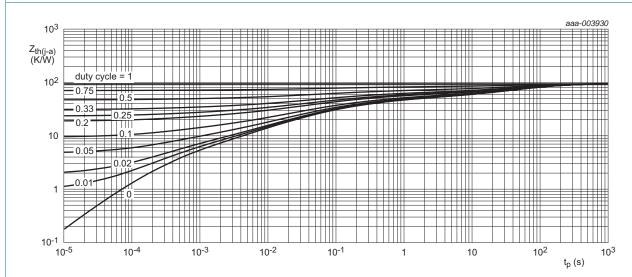


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics (per transistor)					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
I_{GSS}	gate leakage current	$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	10	μΑ
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
R _{DSon}	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -1.3 \text{ A}; T_j = 25 \text{ °C}$	-	82	103	$m\Omega$
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -1.3 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	114	144	mΩ
		V_{GS} = -2.5 V; I_D = -1.1 A; T_j = 25 °C	-	107	146	mΩ
		V_{GS} = -1.8 V; I_{D} = -0.8 A; T_{j} = 25 °C	-	142	210	$m\Omega$
g _{fs}	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -1.3 \text{ A}; T_j = 25 \text{ °C}$	-	6	-	S
Dynamic ch	aracteristics (per transist	or)				
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -1.3 A; V_{GS} = -4.5 V;	-	5.4	8.1	nC
Q_{GS}	gate-source charge	$T_j = 25 ^{\circ}C$	-	0.7	-	nC
Q_{GD}	gate-drain charge		-	1	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V; } f = 1 \text{ MHz; } V_{GS} = 0 \text{ V;}$	-	514	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	78	-	pF
C _{rss}	reverse transfer capacitance		-	59	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -1.3 A; V_{GS} = -4.5 V;	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 $ °C	-	12	-	ns
t _{d(off)}	turn-off delay time		-	47	-	ns
t _f	fall time		-	21	-	ns
Source-drai	in diode (per transistor)					
V_{SD}	source-drain voltage	$I_S = -0.3 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_i = 25 \text{ °C}$	-	-0.7	-1.2	V

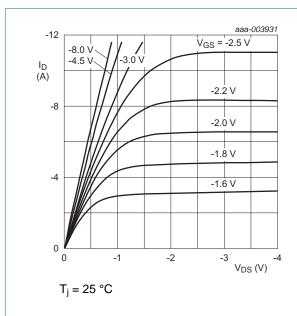


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

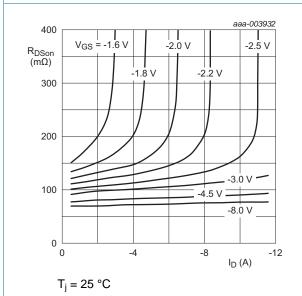
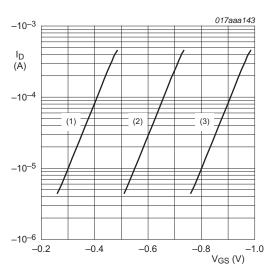


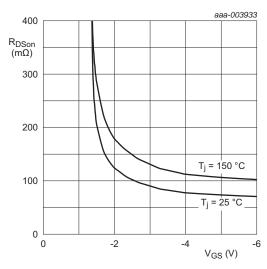
Fig 8. Drain-source on-state resistance as a function of drain current; typical values



 $T_i = 25 \, ^{\circ}C; \, V_{DS} = -3 \, V$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $I_D = -1.3 A$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

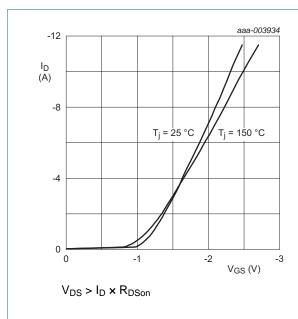


Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

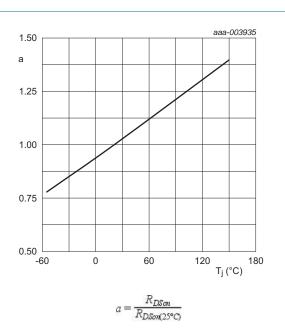


Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

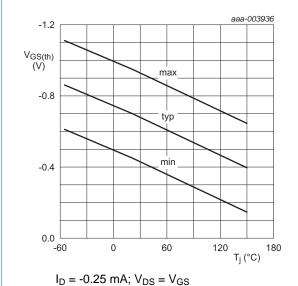


Fig 12. Gate-source threshold voltage as a function of junction temperature

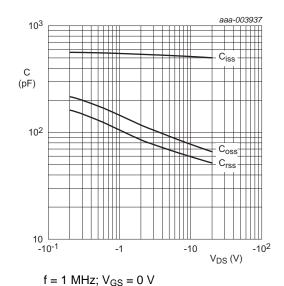
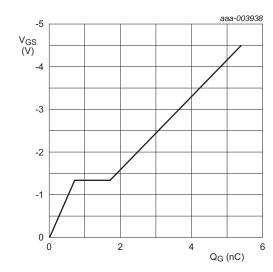


Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 I_D = -1.3 A; V_{DS} = -10 V; T_{amb} = 25 °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

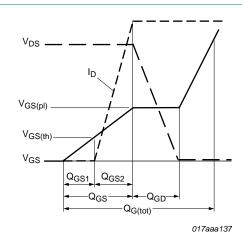
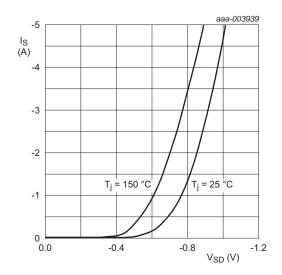


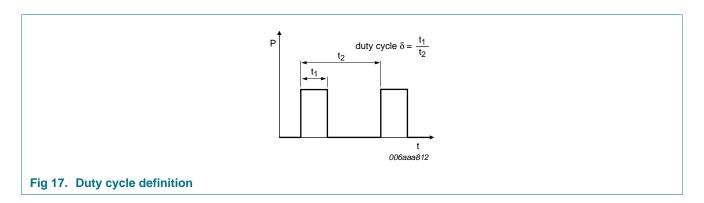
Fig 15. Gate charge waveform definitions



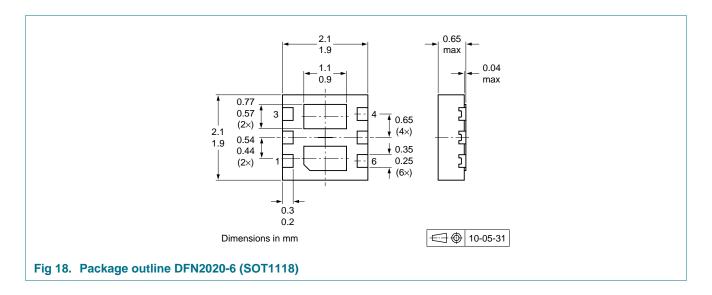
 $V_{GS} = 0 V$

Fig 16. Source current as a function of source-drain voltage; typical values

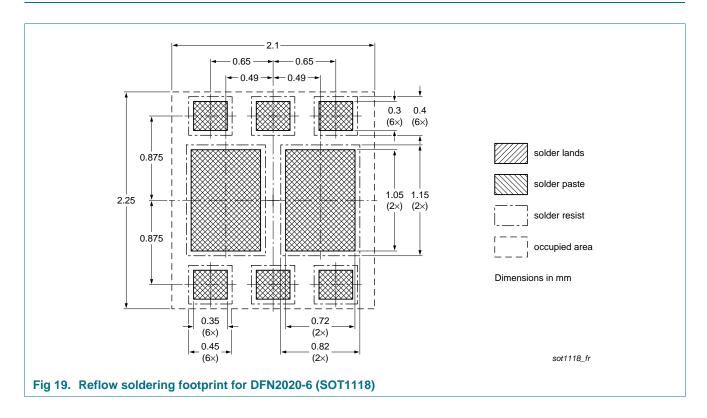
8. Test information



9. Package outline



10. Soldering



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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMDPB85UPE v.1	20120620	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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